

**GUJARAT TECHNOLOGICAL UNIVERSITY****BE- SEMESTER-V (NEW) EXAMINATION – WINTER 2020****Subject Code:3151105****Date:03/02/2021****Subject Name:VLSI Design****Time:10:30 AM TO 12:30 PM****Total Marks: 56****Instructions:**

1. Attempt any FOUR questions out of EIGHT questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

		<b>MARKS</b>
<b>Q.1</b>	(a) Draw CMOS inverter circuit and cross section view of nMOSFET.	<b>03</b>
	(b) Draw voltage transfer characteristics of inverter and define $V_{IL}$ , $V_{IH}$ , $V_{OL}$ , $V_{OH}$ , $NM_L$ and $NM_H$ .	<b>04</b>
	(c) Derive threshold voltage equation and explain what is substrate bias effect.	<b>07</b>
<b>Q.2</b>	(a) Realize following Boolean logic equation using CMOS inverter. $Z = (AB + C(D + E))'$	<b>03</b>
	(b) Compare Static and Dynamic logic circuit.	<b>04</b>
	(c) Derive drain current using gradual channel approximation.	<b>07</b>
<b>Q.3</b>	(a) Draw VTC of CMOS inverter and find operating region of NMOS and PMOS at different input voltage ranges from 0 to V <sub>DD</sub> .	<b>03</b>
	(b) Derive Critical voltages $V_{IL}$ and $V_{IH}$ of CMOS inverter	<b>04</b>
	(c) Consider a CMOS inverter with the following parameters: $V_{Ton} = 0.6$ V, $V_{Top} = -0.7$ V, $K_n' = 50$ $\mu\text{A}/\text{V}^2$ , $K_p' = 16$ $\mu\text{A}/\text{V}^2$ , $(W/L)_n = 4$ , $(W/L)_p = 5$ . Calculate the noise margins of this circuit. The power supply voltage is $V_{DD} = 3.3$ V.	<b>07</b>
<b>Q.4</b>	(a) Draw resistive load inverter circuit and its VTC curve.	<b>03</b>
	(b) Derive critical voltages $V_{OH}$ , $V_{OL}$ , $V_{IL}$ and $V_{IH}$ of resistive load inverter.	<b>04</b>
	(c) Design resistive load inverter with following parameters: $V_{Ton} = 0.8$ V, $K_n' = 20$ $\mu\text{A}/\text{V}^2$ , $(W/L)_n = 2$ , $R_L = 200$ kohm and $V_{DD} = 5$ V. Calculate the noise margins of this circuit.	<b>07</b>
<b>Q.5</b>	(a) Draw transistor level circuit diagram of NOR based SR latch using CMOS.	<b>03</b>
	(b) Derive switching power dissipation equation of CMOS inverter with idea step input.	<b>04</b>
	(c) Justify importance of transmission gate. Realize following functions using TG. i) $F = AB + A'C' + AB'C$ and ii) $F = AB' + A'B$	<b>07</b>
<b>Q.6</b>	(a) What is need of domino CMOS logic circuit and draw it's circuit diagram.	<b>03</b>

- (b) Explain Ring oscillator **04**  
(c) Draw i/p and o/p waveform during high to low transition of o/p for CMOS inverter and derive expression for  $\tau_{PHL}$  using differential equation method. **07**
- Q.7** (a) Draw CMOS implementation of D latch with two inverters and two CMOS TG gates. **03**  
(b) Compare CPLD and FPGA. **04**  
(c) Draw and Explain different clock generator and distributor circuits **07**
- Q.8** (a) Compare FinFET and Planar MOSFET **03**  
(b) Compare constant voltage and constant field scaling. **04**  
(c) What is need of Design of Testability (DFT) in VLSI IC design and explain Built in Self Test (BIST) techniques of DFT. **07**

\*\*\*\*\*

GTUQuestionPapers.com